

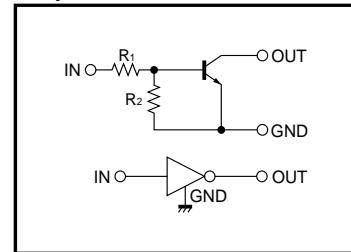
Digital transistors (built-in resistors)

DTC115EM / DTC115EE / DTC115EUA DTC115EKA / DTC115ESA

●Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see the equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input, and parasitic effects are almost completely eliminated.
- 3) Only the on/off conditions need to be set for operation, making device design easy.
- 4) Higher mounting densities can be achieved.

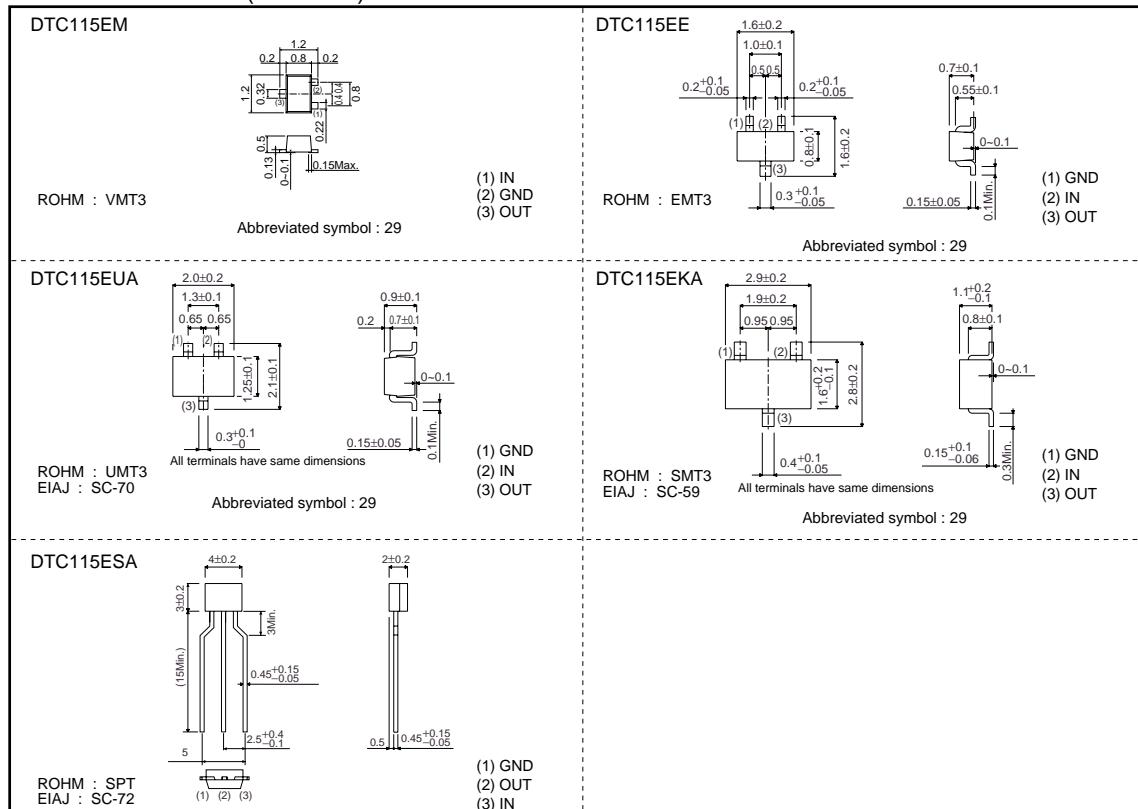
●Equivalent circuit



●Structure

NPN digital transistor (with built-in resistors)

●External dimensions (Units : mm)



DTC115EM / DTC115EE / DTC115EUA

Transistors

DTC115EKA / DTC115ESA

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	Vcc	50	V
Input voltage	Vi	-10~+40	V
Output current	Io	20	mA
	Ic(Max.)	100	
Power dissipation	DTC115EM / DTC115EE	150	
	DTC115EUA / DTC115EKA	200	mW
	DTC115ESA	300	
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55~+150	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V _{i(off)}	—	—	0.5	V	V _{cc} =5V, I _o =100μA
	V _{i(on)}	3	—	—		V _o =0.3V, I _o =1mA
Output voltage	V _{o(on)}	—	0.1	0.3	V	I _o =5mA, I _i =0.25mA
Input current	I _i	—	—	0.15	mA	V _i =5V
Output current	I _{o(off)}	—	—	0.5	μA	V _{cc} =50V, V _i =0V
DC current gain	G _i	82	—	—	—	I _o =5mA, V _o =5V
Input resistance	R _i	70	100	130	kΩ	—
Resistance ratio	R _o /R _i	0.8	1	1.2	—	—
Transition frequency	f _t	—	250	—	MHz	V _{ce} =10V, I _e =5mA, f=100MHz

*Transition frequency of the device.

●Package, marking, and packaging specifications

Type	DTC115EM	DTC115EE	DTC115EUA	DTC115EKA	DTC115ESA
Package	VMT3	EMT3	UMT3	SMT3	SPT
Marking	29	29	29	29	—
Packaging code	T2L	TL	T106	T146	TP
Basic ordering unit (pieces)	8000	3000	3000	3000	5000